

MSKSEMI 美森科

SEMICONDUCTOR



ESD



TVS



TSS



MOV



GDT



PLED

2SB772

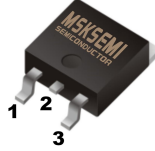
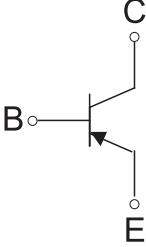
Product specification

TRANSISTOR (PNP)

Reference News

FEATURES

- Low Speed Switching

| PACKAGE OUTLINE | Equivalent Circuit | Marking |
|---|---|--|
|  <p>1. BASE 2. COLLECTOR 3. EMITTER</p> <p>TO-252</p> |  | <div style="background-color: black; color: white; padding: 10px; text-align: center;"> B772P M3Y </div> |

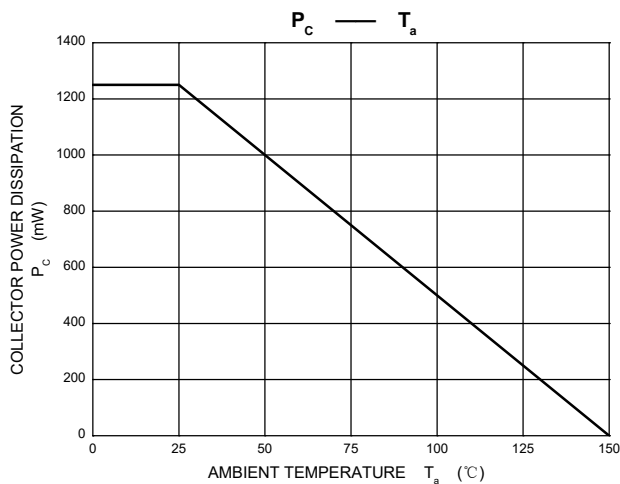
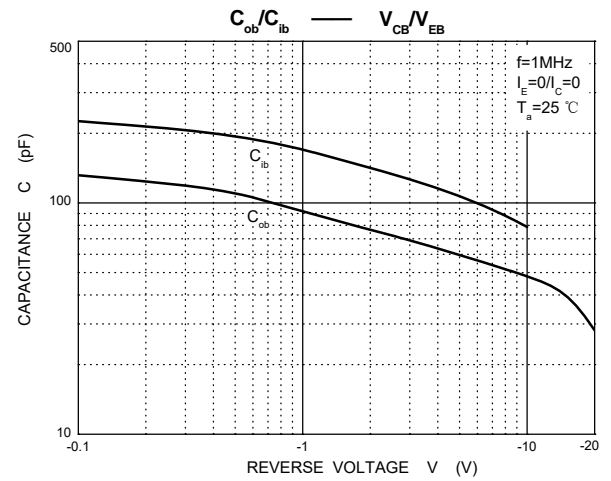
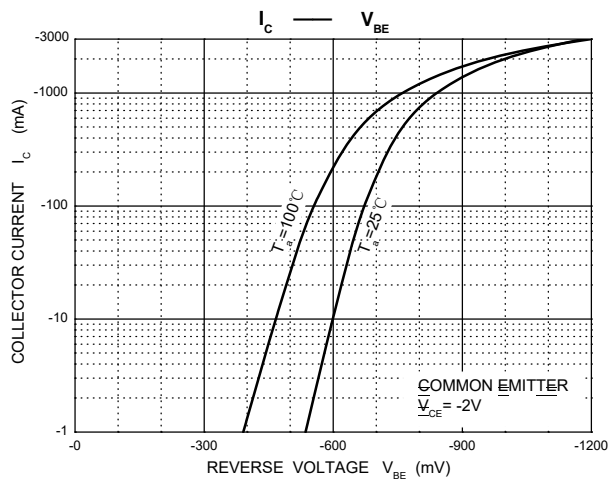
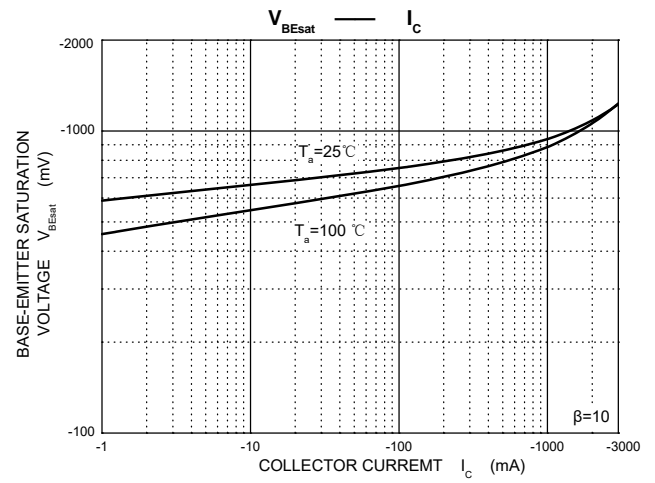
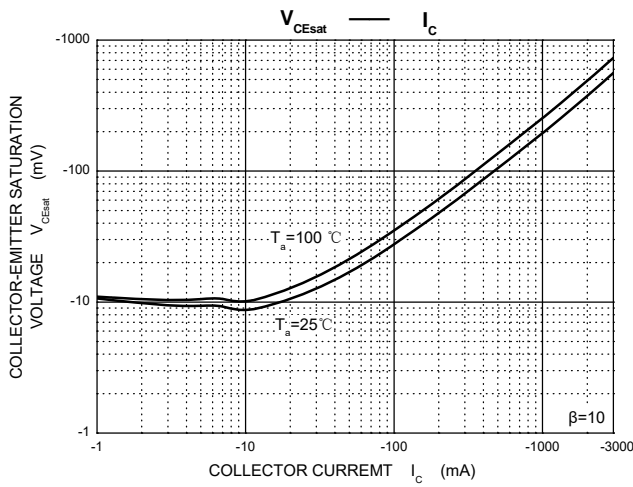
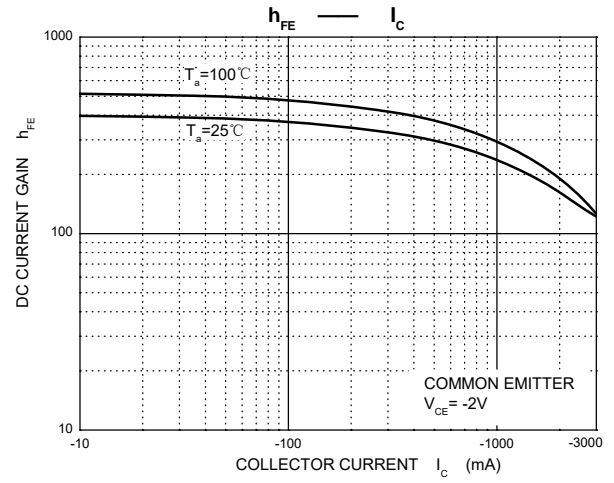
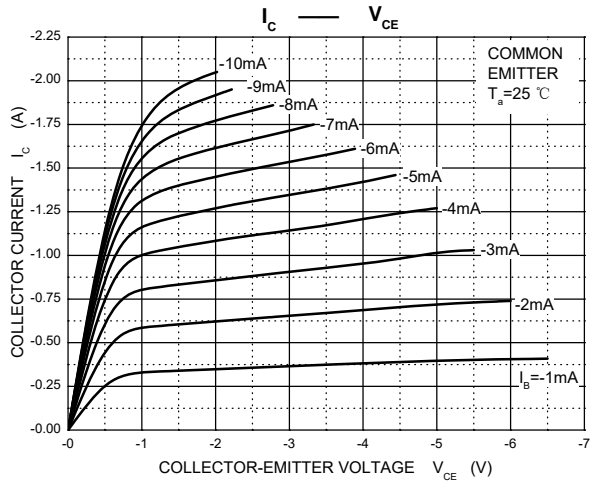
MAXIMUM RATINGS (Ta=25°C unless otherwise noted)

| Symbol | Parameter | Value | Unit |
|-----------------|--|---------|------|
| V_{CBO} | Collector-Base Voltage | -40 | V |
| V_{CEO} | Collector-Emitter Voltage | -30 | V |
| V_{EBO} | Emitter-Base Voltage | -6 | V |
| I_C | Collector Current -Continuous | -3 | A |
| P_C | Collector Power Dissipation | 1.25 | W |
| $R_{\theta JA}$ | Thermal Resistance, junction to Ambient | 100 | °C/W |
| T_J, T_{stg} | Operation Junction and Storage Temperature Range | -55-150 | °C |

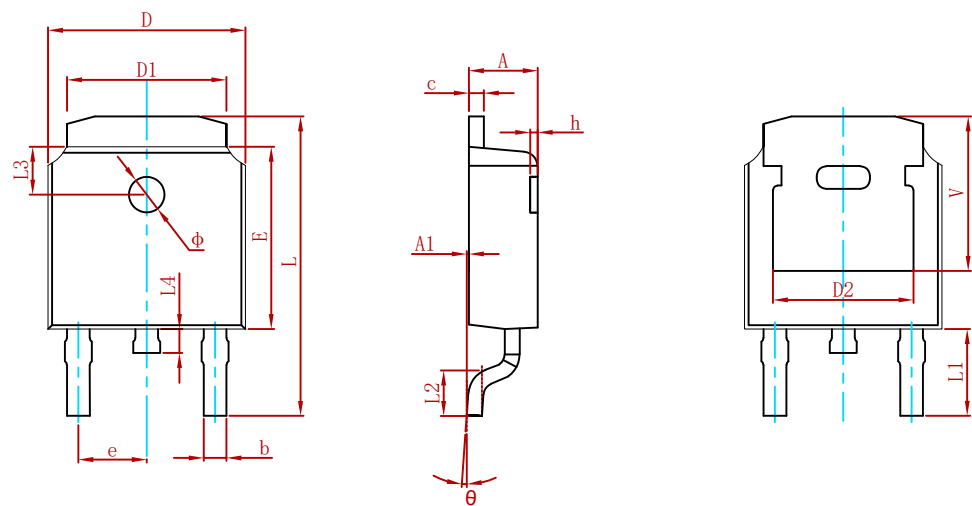
ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

| Parameter | Symbol | Test conditions | Min | Typ | Max | Unit |
|--------------------------------------|---------------|--|-----|-----|------|---------|
| Collector-base breakdown voltage | $V_{(BR)CBO}$ | $I_C = -100\mu A, I_E = 0$ | -40 | | | V |
| Collector-emitter breakdown voltage | $V_{(BR)CEO}$ | $I_C = -10mA, I_B = 0$ | -30 | | | V |
| Emitter-base breakdown voltage | $V_{(BR)EBO}$ | $I_E = -100\mu A, I_C = 0$ | -6 | | | V |
| Collector cut-off current | I_{CBO} | $V_{CB} = -40V, I_E = 0$ | | | -1 | μA |
| Collector cut-off current | I_{CEO} | $V_{CE} = -30V, I_B = 0$ | | | -10 | μA |
| Emitter cut-off current | I_{EBO} | $V_{EB} = -6V, I_C = 0$ | | | -1 | μA |
| DC current gain | h_{FE} | $V_{CE} = -2V, I_C = -1A$ | 160 | | 320 | |
| Collector-emitter saturation voltage | $V_{CE(sat)}$ | $I_C = -2A, I_B = -0.2A$ | | | -0.5 | V |
| Base-emitter saturation voltage | $V_{BE(sat)}$ | $I_C = -2A, I_B = -0.2A$ | | | -1.5 | V |
| Transition frequency | f_T | $V_{CE} = -5V, I_C = -0.1A, f = 10MHz$ | 50 | 80 | | MHz |

Typical Characteristics

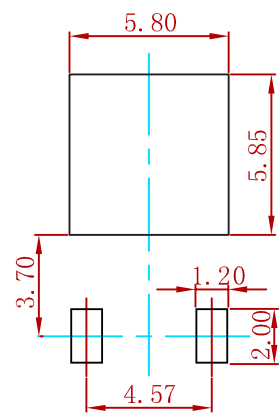


PACKAGE MECHANICAL DATA



| Symbol | Dimensions In Millimeters | | Dimensions In Inches | |
|--------|---------------------------|--------|----------------------|-------|
| | Min. | Max. | Min. | Max. |
| A | 2.200 | 2.400 | 0.087 | 0.094 |
| A1 | 0.000 | 0.127 | 0.000 | 0.005 |
| b | 0.635 | 0.770 | 0.025 | 0.030 |
| c | 0.460 | 0.580 | 0.018 | 0.023 |
| D | 6.500 | 6.700 | 0.256 | 0.264 |
| D1 | 5.100 | 5.460 | 0.201 | 0.215 |
| D2 | 4.830 REF. | | 0.190 REF. | |
| E | 6.000 | 6.200 | 0.236 | 0.244 |
| e | 2.186 | 2.386 | 0.086 | 0.094 |
| L | 9.712 | 10.312 | 0.382 | 0.406 |
| L1 | 2.900 REF. | | 0.114 REF. | |
| L2 | 1.400 | 1.700 | 0.055 | 0.067 |
| L3 | 1.600 REF. | | 0.063 REF. | |
| L4 | 0.600 | 1.000 | 0.024 | 0.039 |
| Φ | 1.100 | 1.300 | 0.043 | 0.051 |
| θ | 0° | 8° | 0° | 8° |
| h | 0.000 | 0.300 | 0.000 | 0.012 |
| V | 5.250 REF. | | 0.207 REF. | |

Syggested Pad Layout



Note:
1.Controlling dimension:in millimeters.
2.General tolerance:± 0.05mm.
3.The pad layout is for reference purposes only.

REELSPECIFICATION

| P/N | PKG | QTY |
|--------|--------|------|
| 2SB772 | TO-252 | 2500 |

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